

Silicon PNP Power Transistors

2SB707 2SB708

DESCRIPTION

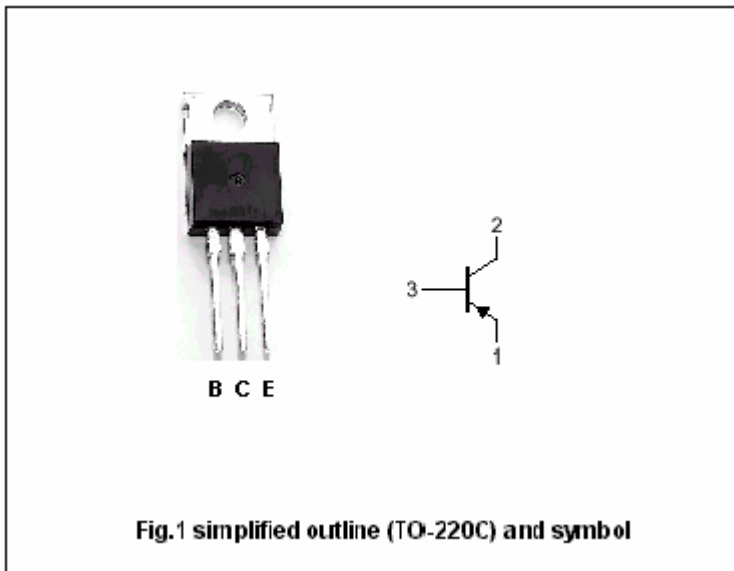
- With TO-220C package
- Complement to type 2SD568/569

APPLICATIONS

- For low frequency power amplifier
- low speed switching industrial use

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-80	V
V <sub>CEO</sub>	Collector-emitter voltage	2SB707 Open base	-60	V
		2SB708	-80	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-7	V
I <sub>C</sub>	Collector current		-7	A
I <sub>CM</sub>	Collector current-peak		-15	A
I <sub>B</sub>	Base current		-3.5	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25	1.5	W
		T <sub>C</sub> =25	40	
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA; I <sub>B</sub> =0	2SB707	-60		V
			2SB708	-80		
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A; I <sub>B</sub> =-0.5 A			-0.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-5A; I <sub>B</sub> =-0.5 A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-60V; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-10	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-1V	40		200	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-5A ; V <sub>CE</sub> =-1V	20			

◆ h<sub>FE-2</sub> classifications

R	O	Y
40-80	60-120	100-200

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PACKAGE OUTLINE

